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## SPECIAL SESSION

### Technology Highlights [Shunju I, II]

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K. Schroefer, Infineon Technologies AG

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**Pipe-Shaped BiCS Flash Memory with 16 Stacked Layers and Multi-Level-Cell Operation for Ultra High Density Storage Devices**, R. Katsumata\*, M. Kito\*, Y. Fukuzumi\*, M. Kido\*, H. Tanaka\*, Y. Komori\*, M. Ishiduki\*, J. Matsunami\*, T. Fujiwara\*, Y. Nagata\*\*\*, L. Zhang\*\*, Y. Iwata\*, R. Kirisawa\*, H. Aochi\* and A. Nitayama\* , \*Toshiba Corporation, Semiconductor Company, \*\*Toshiba Corporation and \*\*\*Toshiba Information Systems (Japan) Corporation, Japan

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